
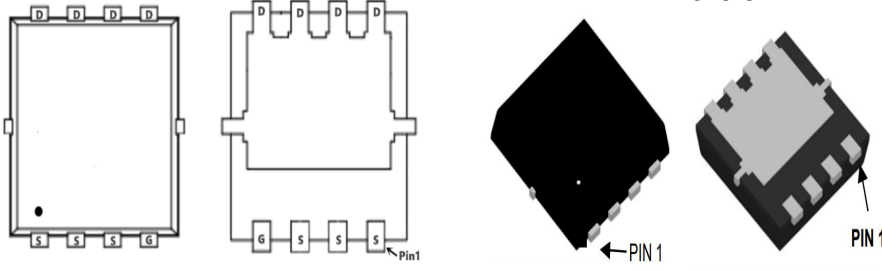


TMN40100NF

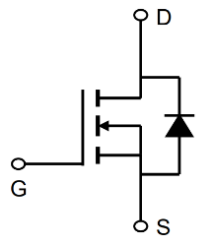
N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 40V$ $I_D = 100A$</p> <p>$R_{DS(ON)} = 4.2m\Omega (typ.) @ V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
--	--

NF:DFN5x6-8L



Marking: 100N04



Absolute Maximum Ratings: ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C = 25^\circ C$	100	A
	Continuous Drain Current- $T_C = 100^\circ C$	57	
	Pulsed Drain Current	360	
E_{AS}	Single Pulse Avalanche Energy	59	mJ
P_D	Power Dissipation	83	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case ²	1.5	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to mbient	62	$^\circ C/W$

TMN40100NF

N-Channel Enhancement Mosfet

Electrical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=40V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics³						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1.2	1.6	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ²	$V_{GS}=10V, I_D=20A$	---	4.2	5.5	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	5.3	7	
G_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=2A$	---	16.5	---	S
Dynamic Characteristics⁴						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	2400	3580	pF
C_{oss}	Output Capacitance		---	220	380	
C_{rss}	Reverse Transfer Capacitance		---	150	220	
Switching Characteristics⁴						
$t_{d(on)}$	Turn-On Delay Time 3, 4	$V_{DD}=15V, I_D=1A, R_G=3.3\Omega$ $V_{GS}=10V$	---	14.2	28	ns
t_r	Rise Time 3, 4		---	18.3	36	ns
$t_{d(off)}$	Turn-Off Delay Time 3, 4		---	38.8	76	ns
t_f	Fall Time 3, 4		---	13.9	28	ns
Q_g	Total Gate Charge 3, 4	$V_{GS}=4.5V, V_{DS}=32V,$ $I_D=10A$	---	25	50	nC
Q_{gs}	Gate-Source Charge 3, 4 3, 4		---	6.4	13	nC
Q_{gd}	Gate-Drain "Miller" Charge 3, 4		---	12.1	24	nC
Drain-Source Diode Characteristics						
Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{SD}	Source-Drain Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A$	---	---	1	V
LS	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	100	A
LSM	Pulsed Source Current		---	---	180	A

Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

TMN40100NF

N-Channel Enhancement Mosfet

Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

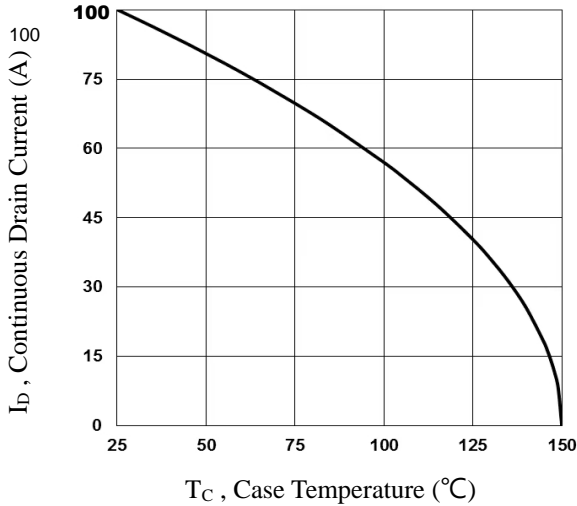


Fig.1 Continuous Drain Current vs. T_C

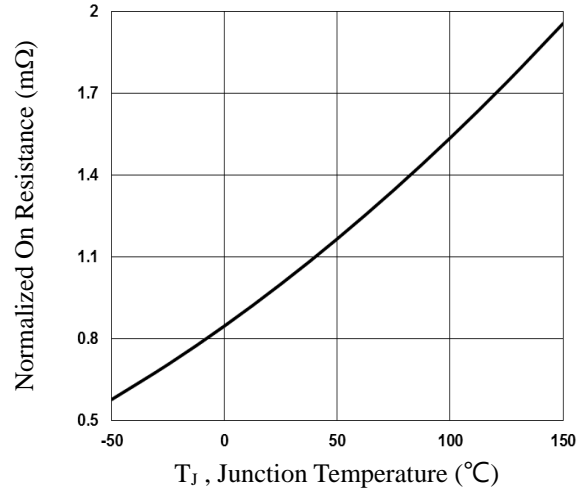


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

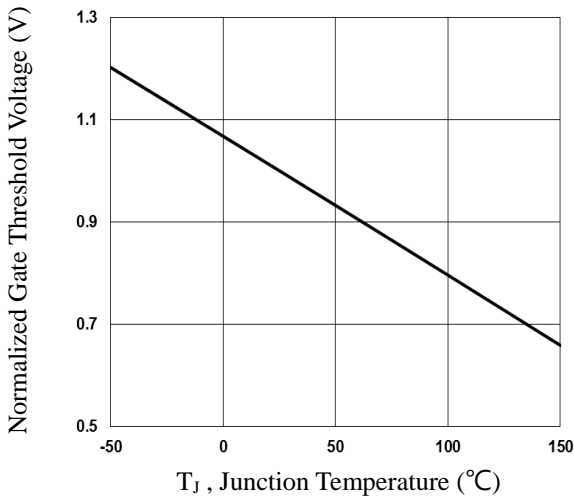


Fig.3 Normalized V_{th} vs. T_J

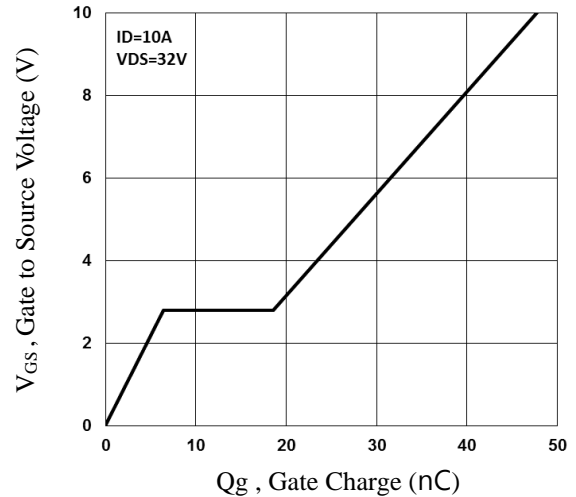


Fig.4 Gate Charge Waveform

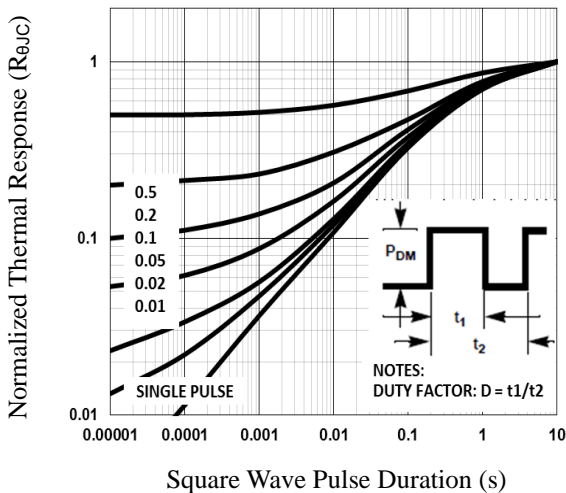


Fig.5 Normalized Transient Impedance

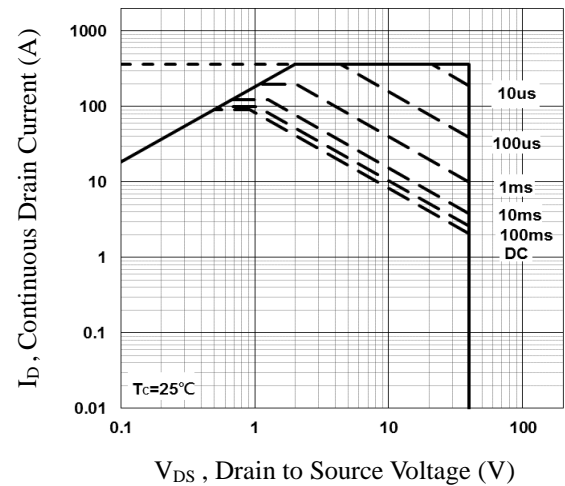


Fig.6 Maximum Safe Operation Area



TMN40100NF

N-Channel Enhancement Mosfet

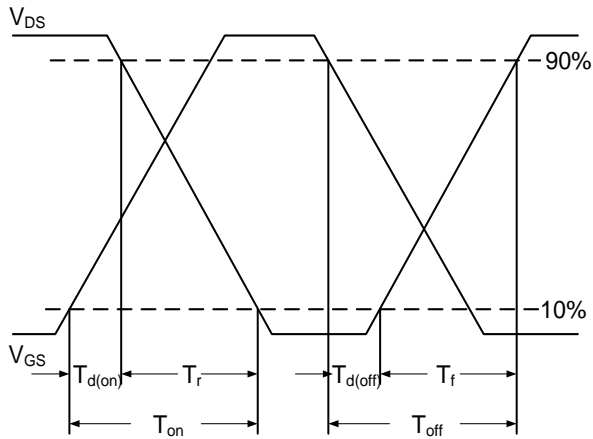


Fig.7 Switching Time Waveform

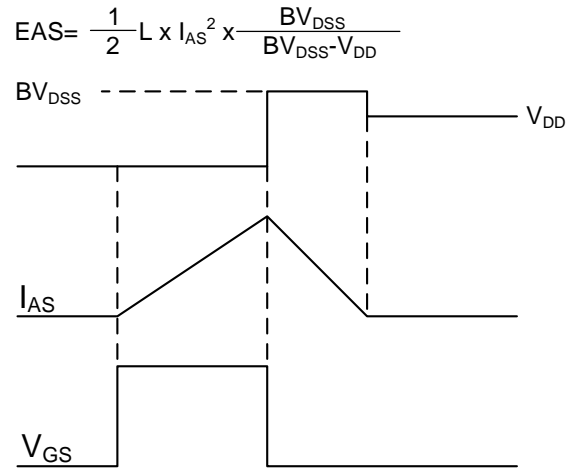
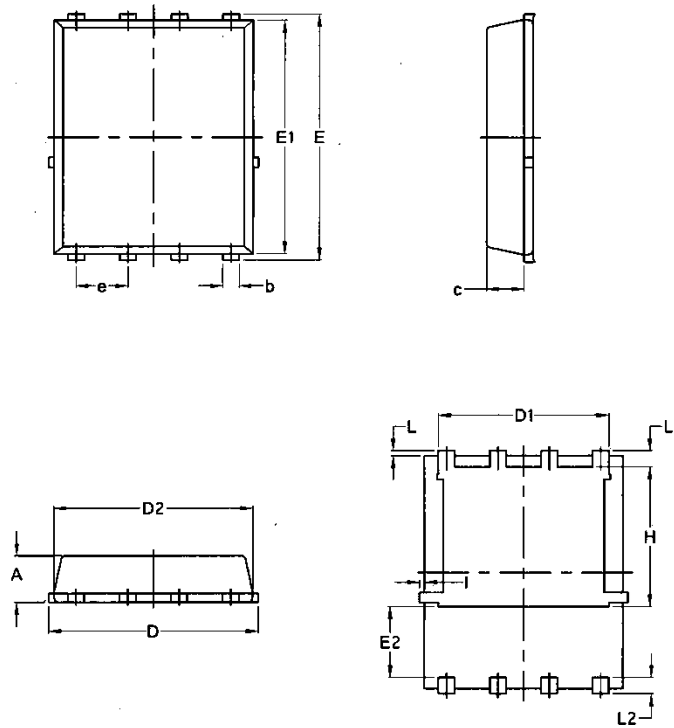


Fig.8 EAS Waveform

Package Mechanical Data:DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Tritech-MOS](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#)
[BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#) [DMNH15H110SK3-13](#) [SLF10N65ABV2](#)
[BSO203SP](#) [BSO211P](#) [IPA60R230P6](#) [IPA60R460CE](#)